

## Ligand and Solvent Effects on Hole Transport in PbS Quantum Dot Assemblies

○Liming Liu<sup>1,2</sup>, Satria Zulkarnaen Bisri<sup>1</sup>, Yasuhiro Ishida<sup>1</sup>, Yoshihiro Iwasa<sup>1,2</sup> and Takuzo Aida<sup>1,2</sup>

1 RIKEN-CEMS, 2 Tokyo Univ.

E-mail: liming.liu@riken.jp, satria.bisri@riken.jp

Semiconductor quantum dots (QDs) in colloidal form have attracted growing interest for their potential applications in solution-processable electronic devices. Controlled electronic doping in QD assemblies is one of the challenges required for advancing the development of novel solar cells<sup>[1]</sup>, photodetectors, and transistors based on this system. While several n-type QD films with excellent conductivity have been successfully demonstrated, in general, p-type QD films have shown poor conductivity. Ligand and solvent engineering were found to permit significant enhancements of hole transport in lead sulfide (PbS) QD films. Capping with a carboxylate ligand generally produces p-type doping of PbS QD films (Figure. 1); furthermore, among various carboxylate ligands, thiophene-2,5-dicarboxylic acid provides PbS QD films with exceptionally high hole mobility values, and solvents with a high solvency power for the ligand are important for enhancing carrier mobility.<sup>[2]</sup> With an appropriate combination of ligand molecule and solvent, QDs can be packed more closely into films, resulting in orders-of-magnitude enhancement in the field-effect hole mobility, reaching values of  $0.20 \pm 0.06 \text{ cm}^2 \cdot \text{V}^{-1} \cdot \text{s}^{-1}$ . The new guideline presented in this study will be vital for constructing high-performance QD-based p-n junction-type devices, especially photovoltaics.

Reference:

[1] Kramer, Illan J., and Edward H. Sargent. *Chemical Reviews* 114.1 (2013): 863-882.

[2] Liu et al. *ACS applies nano material*, submitted.

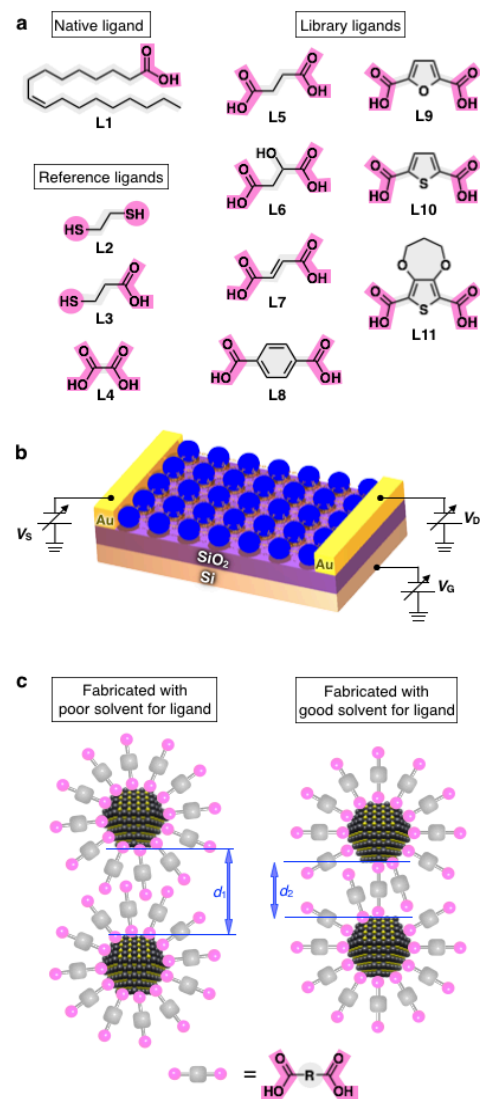


Figure 1. (a) Chemical structures of ligands for capping lead sulfide (PbS) quantum dots (QDs). (b) Schematic illustration of an FET device of a PbS QD film. (c) Effect of the solvent used for fabrication of the FETs on the packing of PbS QDs.